N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed
- Small Footprint DFN3x2-8L package

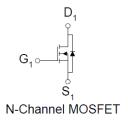
Typical Applications:

- Telecom DC/DC converters
- · White LED boost converters
- Industrial DC/DC conversion
- Automotive Entertainment and GPS DC/DC conversion

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
150	700 @ V _{GS} = 10V	1.3	
130	1200 @ V _{GS} = 4.5V	1	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			150	V			
Gate-Source Voltage	V_{GS}	±20	V				
Continuous Drain Current ^a	T _A =25°C	· I _D	1.3				
Continuous Diain Current	T _A =70°C	טי	1.1	Α			
Pulsed Drain Current ^b		I _{DM}	±10				
Continuous Source Current (Diode Conduction) a		I _S	3	Α			
Power Dissipation ^a	T _A =25°C	P _D	2.5	W			
Power Dissipation	T _A =70°C	ľВ	1.6	V V			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	50	°C/W			
Maximum Junction-to-Ambient	Steady State	ГХ⊕ЈА	90	C/VV			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

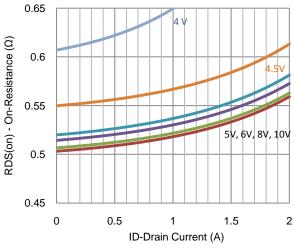
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1		3.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zoro Coto Voltago Drain Current	1	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 1.3 \text{ A}$			700	'00 mΩ	
Dialii-Source Off-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$			1200	11122	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 1.3 \text{ A}$		11		S	
Diode Forward Voltage	V_{SD}	$I_S = 1.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.8		V	
		Dynamic					
Total Gate Charge	Q_g			2.5			
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 1 \text{ A}$		1		nC	
Gate-Drain Charge	Q_{gd}			0.8			
Turn-On Delay Time	t _{d(on)}			5			
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω , I_D = 1 A,		5		nC	
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = 10 V, R_{GEN} = 6 Ω		6		nS	
Fall Time	t _f			4			
Input Capacitance	C _{iss}			320			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		37		pF	
Reverse Transfer Capacitance	C_{rss}			20			

Notes

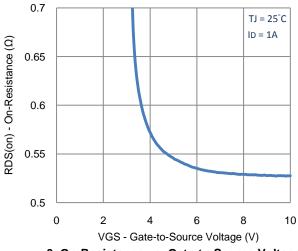
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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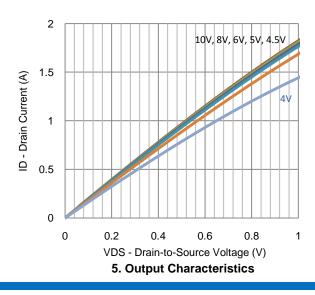
Typical Electrical Characteristics

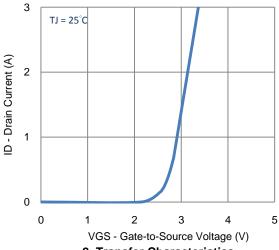


1. On-Resistance vs. Drain Current

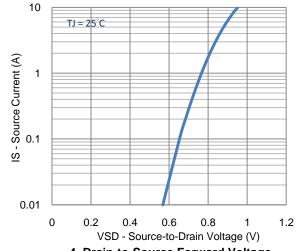


3. On-Resistance vs. Gate-to-Source Voltage

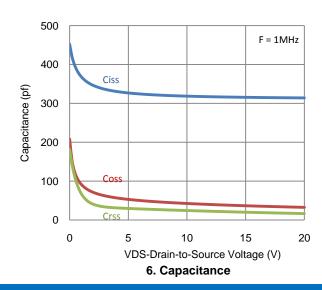




2. Transfer Characteristics

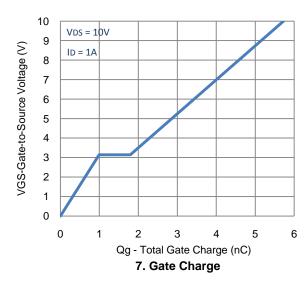


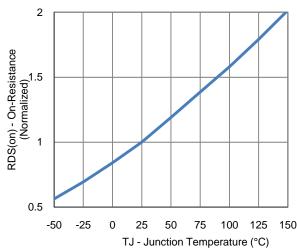
4. Drain-to-Source Forward Voltage

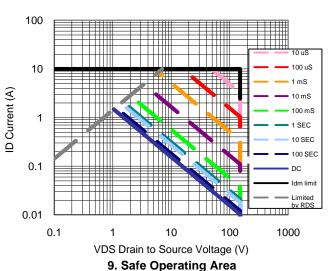


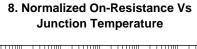
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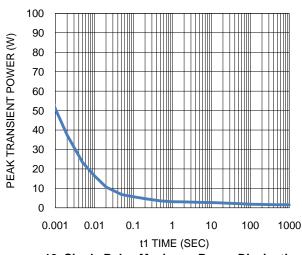
Typical Electrical Characteristics



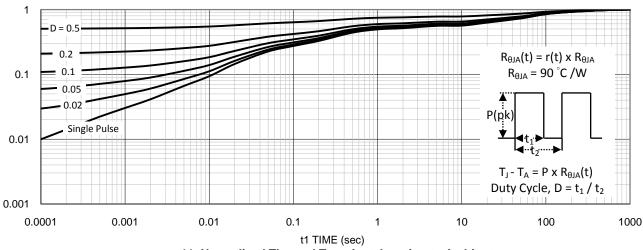






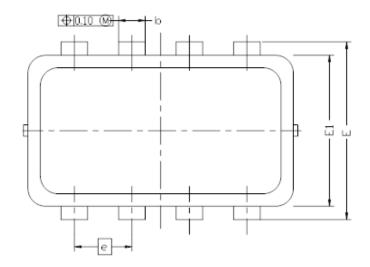


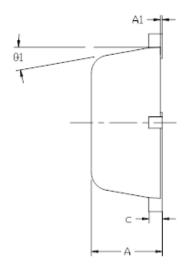


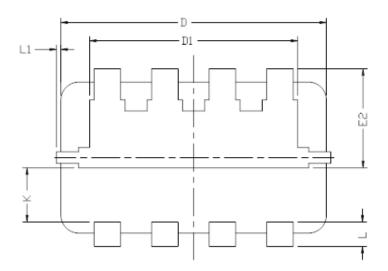


11. Normalized Thermal Transient Junction to Ambient

Package Information







DIM.	MILLIMETERS			INCHES			
DII'I.	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.700	0.80	0.900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0.000		0.002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
	0.08	0.152	0.25	0.003	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2.30	2.35	2.40	0.091	0.093	0.095	
E	2.00 BSC			0.079 BSC			
E1	1	1.70 BSC			0.067 BSC		
E5	1.065	1.115	1.165	0.042	0.044	0.046	
6	0	0.65 BSC			0.026 BSC		
L	0.20	0.275	0.400	0.008	0.011	0.0157	
K	0.56	0.61	0.66	0.022	0.024	0.026	
L1	0		0.100	0		0.004	
θ1	0	10	12	0	10	12	

Note:

- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.

Ordering Information

AM5350N-T1-XX

A: Analog Power

- M: MOSFET

5350: Part numberN: N-ChannelTape & reel

– XX: Blank: Standard

PF: Leadfree